

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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Keep safety first in your circuit designs!

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# 2SK2590

Silicon N-Channel MOS FET

**RENESAS**

ADE-208-1365A (Z)  
2nd. Edition  
Mar. 2001

## Application

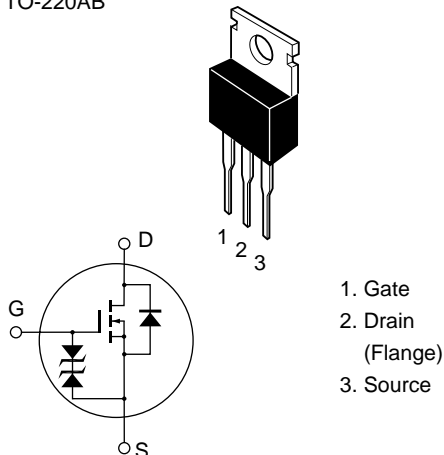
High speed power switching

## Features

- Low on-resistance
- High speed switching
- Low drive current
- No Secondary Breakdown
- Suitable for Switching regulator, DC-DC converter, Motor Control

## Outline

TO-220AB



**Absolute Maximum Ratings** ( $T_a = 25^\circ\text{C}$ )

<b>Item</b>	<b>Symbol</b>	<b>Ratings</b>	<b>Unit</b>
Drain to source voltage	$V_{\text{DSS}}$	200	V
Gate to source voltage	$V_{\text{GSS}}$	$\pm 20$	V
Drain current	$I_{\text{D}}$	7	A
Drain peak current	$I_{\text{D(pulse)}}^{*1}$	28	A
Body to drain diode reverse drain current	$I_{\text{DR}}$	7	A
Channel dissipation	$P_{\text{ch}}^{*2}$	50	W
Channel temperature	$T_{\text{ch}}$	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to +150	$^\circ\text{C}$

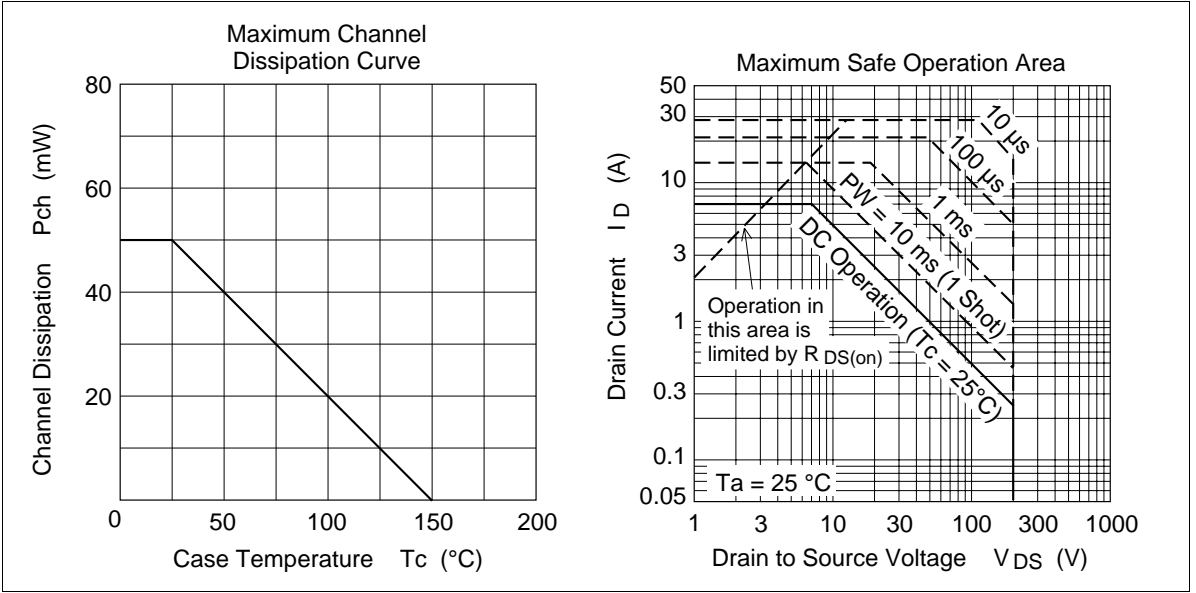
Notes 1. PW 10  $\mu\text{s}$ , duty cycle 1 %  
2. Value at  $T_c = 25^\circ\text{C}$

## Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	200	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	$\pm 20$	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 16 \text{ V}$ , $V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	250	$\mu\text{A}$	$V_{DS} = 160 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	4.0	V	$I_D = 1 \text{ mA}$ , $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.33	0.45		$I_D = 4 \text{ A}$ $V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	3.0	4.5	—	S	$I_D = 4 \text{ A}$ $V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	$C_{iss}$	—	700	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	$C_{oss}$	—	260	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	45	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	20	—	ns	$I_D = 4 \text{ A}$
Rise time	$t_r$	—	45	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	50	—	ns	$R_L = 7.5$
Fall time	$t_f$	—	35	—	ns	
Body to drain diode forward voltage	$V_{DF}$	—	1.1	—	V	$I_F = 7 \text{ A}$ , $V_{GS} = 0$
Body to drain diode reverse recovery time	$t_{rr}$	—	150	—	ns	$I_F = 7 \text{ A}$ , $V_{GS} = 0$ , $di_F / dt = 100 \text{ A} / \mu\text{s}$

Note 1. Pulse Test

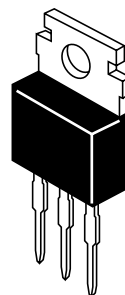
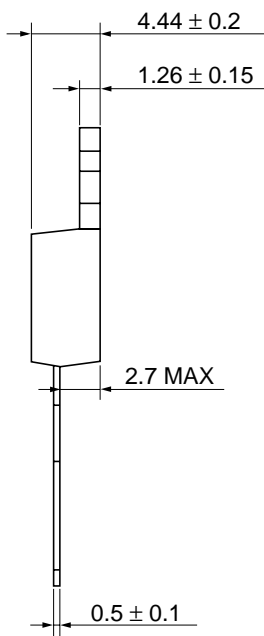
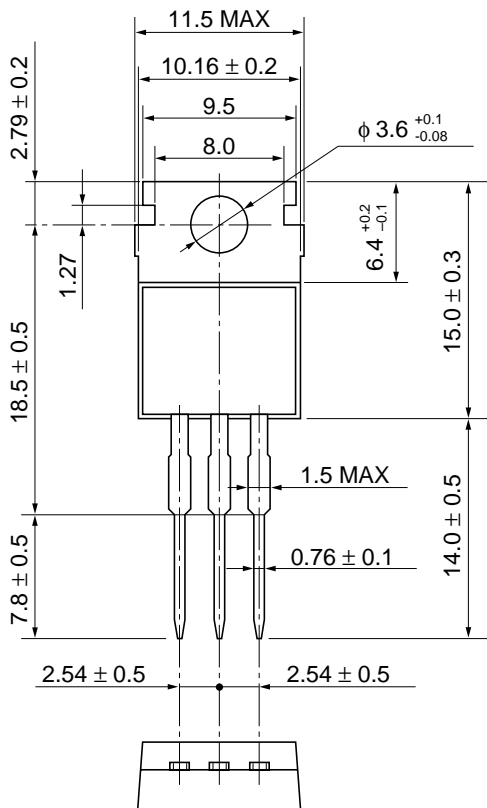
See characteristics curves of 2SK1957.



Package Dimensions

As of January, 2001

Unit: mm



Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	1.8 g

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